

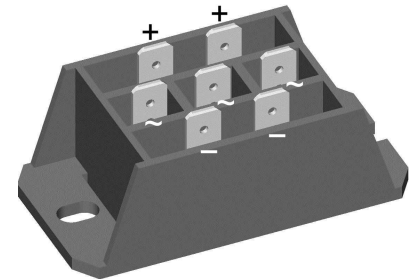
# Standard Rectifier Module

<b>3~ Rectifier</b>	
$V_{RRM} =$	1800 V
$I_{DAV} =$	45 A
$I_{FSM} =$	300 A

## 3~ Rectifier Bridge

Part number

**VUO30-18NO3**



E72873



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

### Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

### Package: FO-F

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- 1/4" fast-on terminals
- Easy to mount with two screws
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

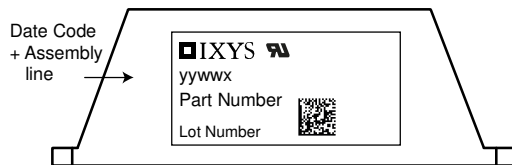
- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

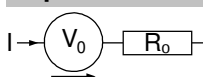
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1900	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1800	V
$I_R$	reverse current	$V_R = 1800$ V		$T_{VJ} = 25^\circ\text{C}$		40	$\mu\text{A}$
		$V_R = 1800$ V		$T_{VJ} = 150^\circ\text{C}$		1.5	mA
$V_F$	forward voltage drop	$I_F = 15$ A		$T_{VJ} = 25^\circ\text{C}$		1.10	V
		$I_F = 45$ A				1.38	V
		$I_F = 15$ A		$T_{VJ} = 125^\circ\text{C}$		1.01	V
		$I_F = 45$ A				1.38	V
$I_{DAV}$	bridge output current	$T_C = 110^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		45	A
		rectangular	$d = \frac{1}{3}$				
$V_{FO}$	threshold voltage			$T_{VJ} = 150^\circ\text{C}$		0.80	V
$r_F$	slope resistance					12.9	m $\Omega$
						} for power loss calculation only	
$R_{thJC}$	thermal resistance junction to case					2	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.4		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		60	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		300	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		325	A
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		255	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		275	A
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		450	A <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		440	A <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		325	A <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		315	A <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		10	pF

Package FO-F				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$I_{RMS}$	RMS current	per terminal			100	A	
$T_{VJ}$	virtual junction temperature		-40		150	°C	
$T_{op}$	operation temperature		-40		125	°C	
$T_{stg}$	storage temperature		-40		125	°C	
<b>Weight</b>					45	g	
$M_D$	mounting torque		2		2.5	Nm	
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	18.0	6.0		mm	
$d_{Spb/Apb}$		terminal to backside	26.0	20.0		mm	
$V_{ISOL}$	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3600		V	
		t = 1 minute				3000	V

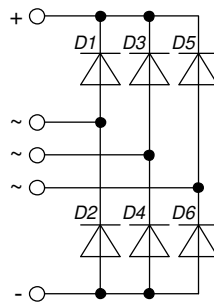
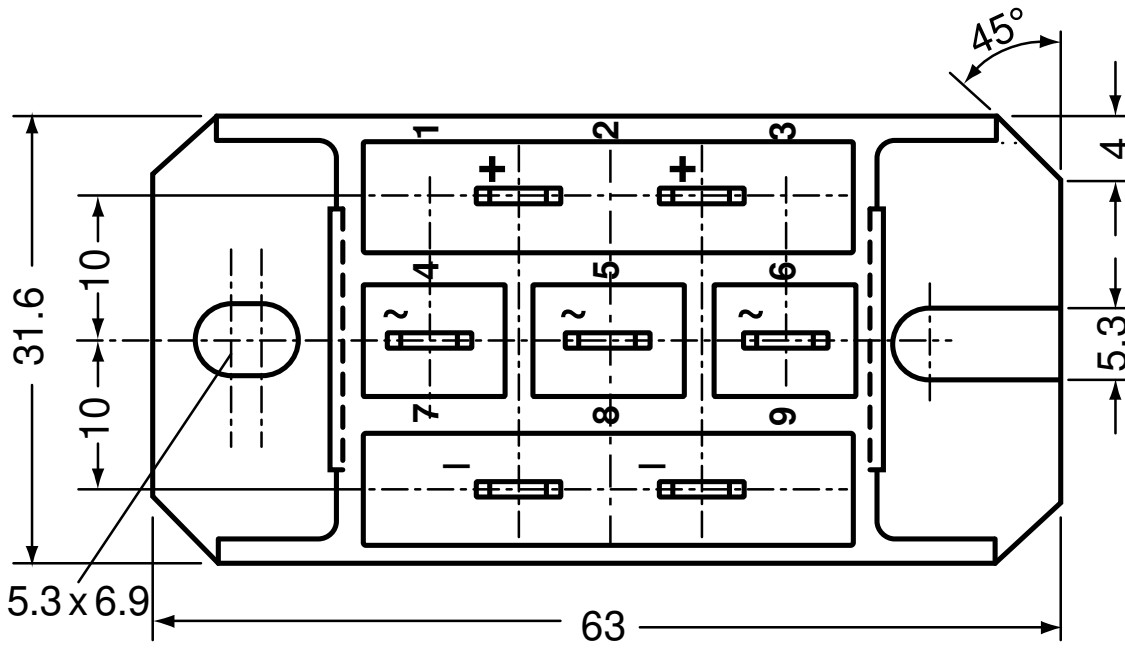
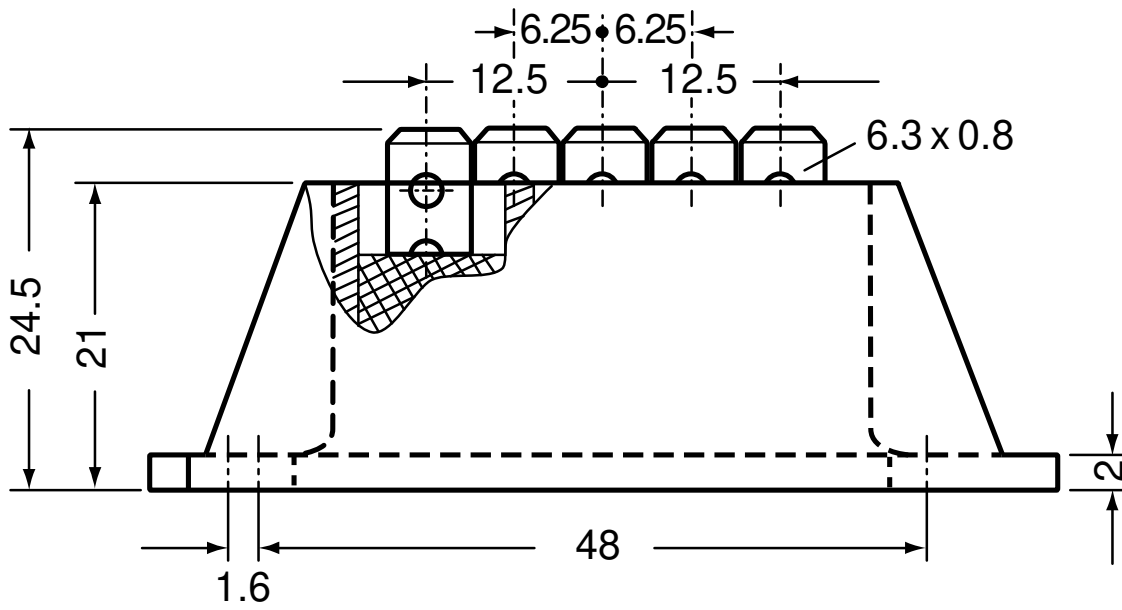


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO30-18NO3	VUO30-18NO3	Box	10	454362

**Equivalent Circuits for Simulation**
*\* on die level*
 $T_{VJ} = 150\text{ °C}$ 

**Rectifier**

$V_{0\ max}$	threshold voltage	0.8	V
$R_{0\ max}$	slope resistance *	11.7	mΩ

Outlines FO-F



## Rectifier

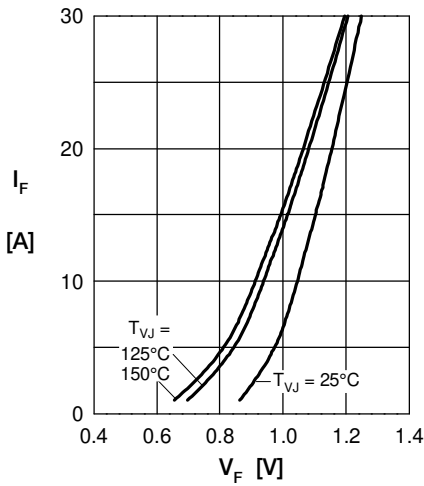


Fig. 1 Forward current vs. voltage drop per diode

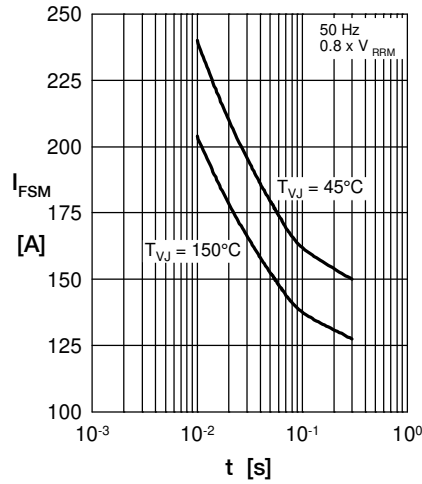


Fig. 2 Surge overload current vs. time per diode

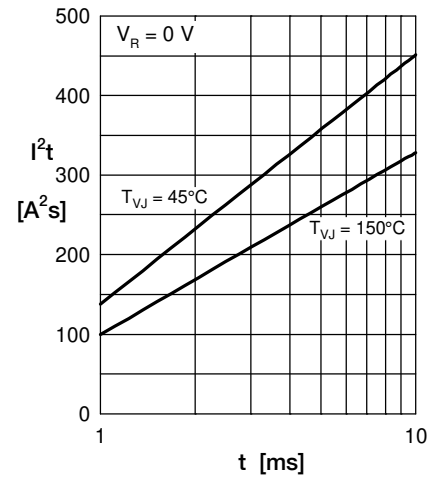


Fig. 3  $I^2t$  vs. time per diode

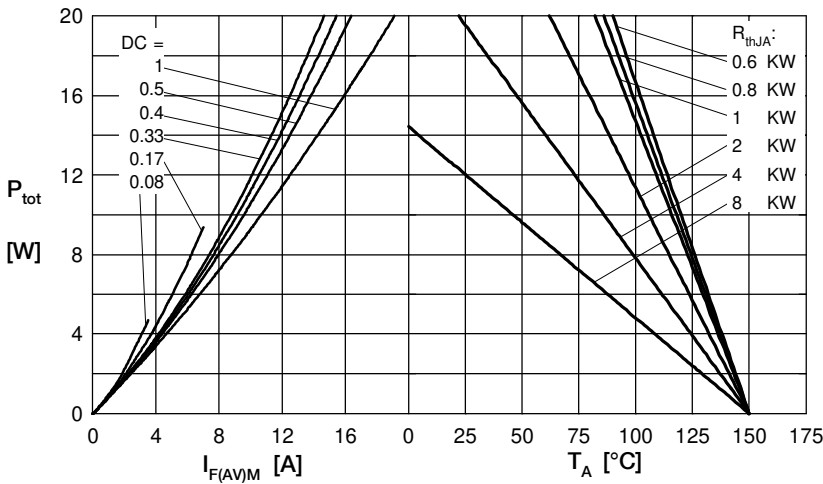


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

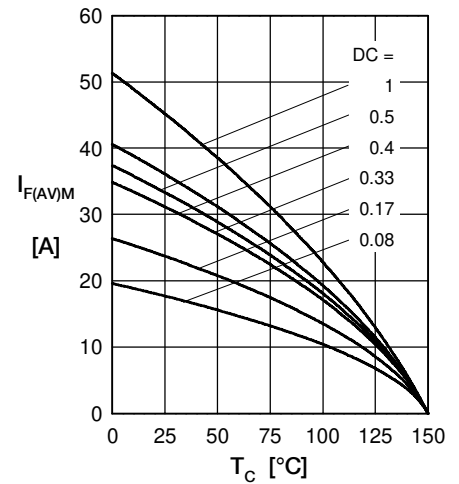


Fig. 5 Max. forward current vs. case temperature per diode

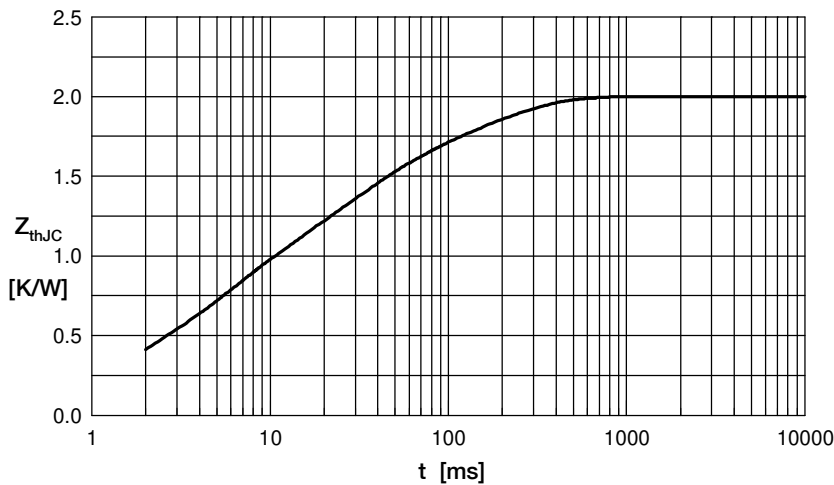


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for  $Z_{thJC}$  calculation:

i	$R_{th}$ (K/W)	$t_i$ (s)
1	0.0607	0.00040
2	0.2030	0.00256
3	0.5005	0.00450
4	0.7030	0.02420
5	0.5328	0.15000